

Phase Control Thyristor

 V_{DRM}

I_{T(AV)}

dl/dt

*Higher dV/dt selections available

Replaces March 1998 version, DS4552-3.3

DS4552-4.0 January 2000

KEY PARAMETERS

3600V

1259A

23750A

300V/us

150Α/μ**s**

APPLICATIONS

- High Power Drives.
- High Voltage Power Supplies.
- DC Motor Control.

FEATURES

- Double Side Cooling.
- High Surge Capability.
- High Mean Current.
- Fatigue Free.

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V _{DRM} V _{RRM} V	Conditions
DCR1277SD36	3600	$T_{vi} = 0^{\circ} \text{ to } 125^{\circ}\text{C},$
DCR1277SD35	3500	$I_{DRM} = I_{RRM} = 150 \text{mA},$
DCR1277SD34	3400	V_{DRM} , V_{RRM} $t_p = 10$ ms,
DCR1277SD33	3300	V _{DSM} & V _{RSM} =
DCR1277SD32	3200	V _{DRM} & V _{RRM} + 100V
		respectively

Lower voltage grades available.

Outline type code: D. See Package Details for further information.

CURRENT RATINGS

T_{case} = 60°C unless stated otherwise.

Symbol	Parameter	Conditions	Max.	Units			
Double Sid	Double Side Cooled						
I _{T(AV)}	Mean on-state current	Half wave resistive load	1259	А			
I _{T(RMS)}	RMS value	-	1977	А			
I _T	Continuous (direct) on-state current	-	1832	А			
Single Side	Single Side Cooled (Anode side)						
I _{T(AV)}	Mean on-state current	Half wave resistive load	885	А			
I _{T(RMS)}	RMS value	-	1390	А			
I _T	Continuous (direct) on-state current	-	1209	А			

CURRENT RATINGS

 $T_{case} = 80^{\circ}C$ unless stated otherwise.

Symbol	Parameter	Conditions	Max.	Units			
Double Sid	Double Side Cooled						
I _{T(AV)}	Mean on-state current	Half wave resistive load	995	А			
I _{T(RMS)}	RMS value	-	1565	А			
I _T	Continuous (direct) on-state current	-	1420	А			
Single Side	Single Side Cooled (Anode side)						
I _{T(AV)}	Mean on-state current	Half wave resistive load	690	А			
I _{T(RMS)}	RMS value	-	1085	А			
I _T	Continuous (direct) on-state current	-	920	А			

SURGE RATINGS

SURGE K	ATINGS	4_		
Symbol	Parameter	Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	19.0	kA
l²t	I ² t for fusing	$V_{R} = 50\% V_{RRM} - 1/4 \text{ sine}$	1.8 x 10 ⁶	A²s
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	23.75	kA
l²t	I ² t for fusing	$V_R = 0$	2.82 x 10 ⁶	A ² s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
		Double side cooled	dc	-	0.020	°C/W
R _{th(j-c)}	R _{th(j-c)} Thermal resistance - junction to case	Single side cooled	Anode dc	-	0.036	°C/W
			Cathode dc	-	0.044	°C/W
	R _{th(c-h)} Thermal resistance - case to heatsink Clamping force 22.0kN with mounting compound	Double side	-	0.004	°C/W	
R _{th(c-h)}		Single side	-	0.008	°C/W	
_	Virtual impetion to report up	On-state (conducting)		-	135	°C
$T_{v_{j}}$	Virtual junction temperature	Reverse (blocking)		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
-	Clamping force			20.0	24.0	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions		Тур.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	150	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% V_{DRM} $T_j = 125$ °C.		-	300	V/μs
		From 67% V _{DRM} to 1000A	Repetitive 50Hz	-	100	A/μs
dl/dt	Rate of rise of on-state current	Gate source $10^{\circ}V$, 5Ω $t_{r} \le 0.5\mu s$, $T_{r} = 125^{\circ}C$	Non-repetitive	-	150	A/μs
V _{T(TO)}	Threshold voltage	At T _{vj} = 125°C		-	0.95	V
r _T	On-state slope resistance	At T _{vj} = 125°C		-	0.45	mΩ
t _{gd}	Delay time	$V_D = 67\%$ V_{DRM} , Gate source 30V, 15Ω $t_r = 0.5 \mu s$, $T_j = 25 ^{\circ} C$		-	2.5	μs
t _q	Turn-off time	$I_T = 2000A$, $t_p = 1$ ms, $T_j = 125$ °C, $V_R = 50V$, $dI_{RR}/dt = 5A/\mu$ s, $V_{DR} = 67\%$ V_{DRM} , $dV_{DR}/dt = 20V/\mu$ s linear		500	650	μs
IL	Latching current	$T_{j} = 25^{\circ}C, V_{D} = 5V$		700	1000	mA
I _H	Holding current	$T_{j} = 25^{\circ}C, R_{g-k} = \infty$		200	500	mA

I _H	Holding current	$T_{j} = 25^{\circ}C, R_{g-k} = \infty$	200	500	mA
ATE TR	IGGER CHARACTERISTICS AND R	ATINGS COM			
Symbol	Parameter	Conditions		Max.	Units
V _{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C		4.0	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$		400	mA
V_{GD}	Gate non-trigger voltage	At V _{DRM} T _{case} = 125°C		0.25	V
V_{FGM}	Peak forward gate voltage	Anode positive with respect to cathode		30	V
V_{FGN}	Peak forward gate voltage	Anode negative with respect to cathode		0.25	V
V_{RGM}	Peak reverse gate voltage			5	V
I _{FGM}	Peak forward gate current	Anode positive with respect to cathode		10	А
P _{GM}	Peak gate power	See table, fig.4		150	W
$P_{G(AV)}$	Mean gate power			5	W

CURVES

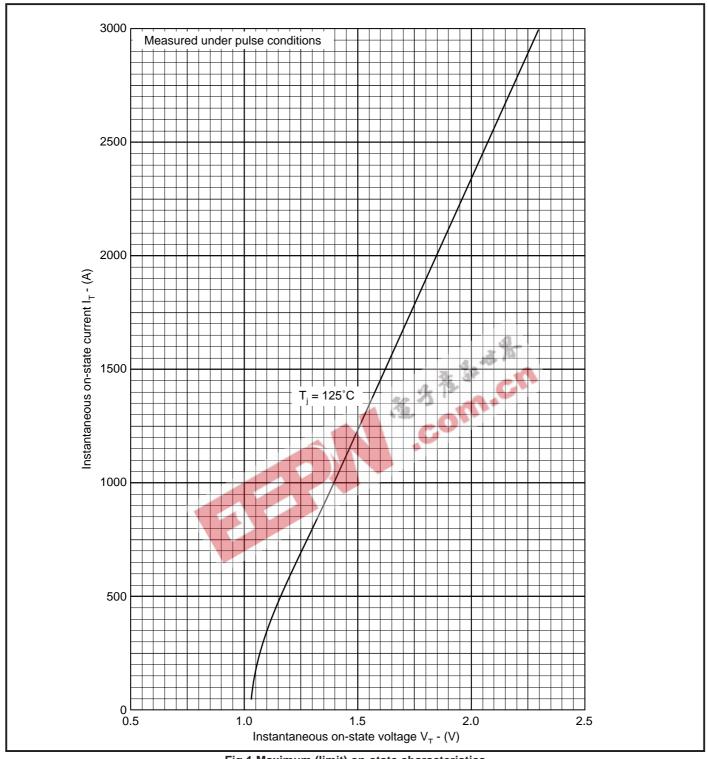


Fig.1 Maximum (limit) on-state characteristics

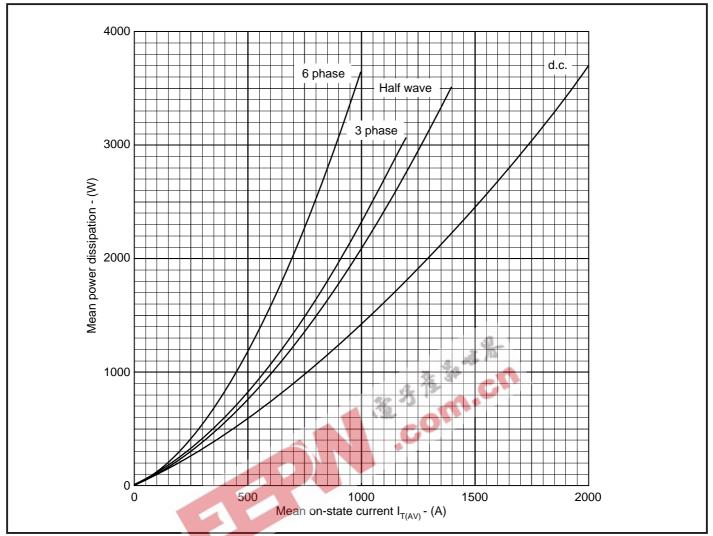


Fig.2 Dissipation curves

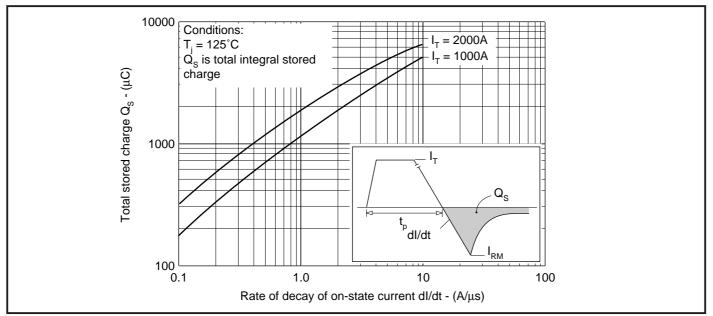


Fig.3 Stored charge

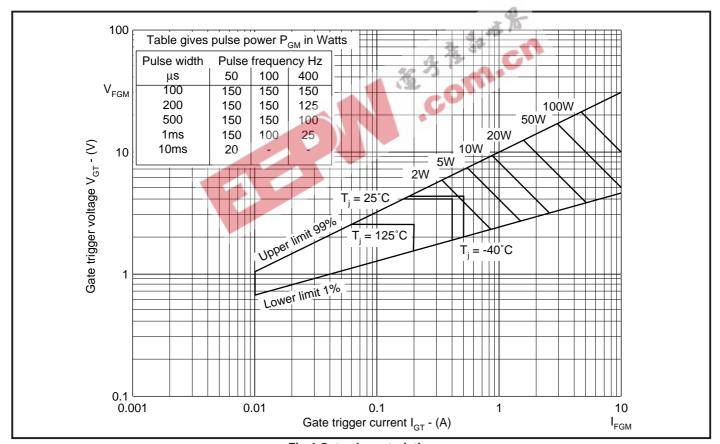


Fig.4 Gate characteristics

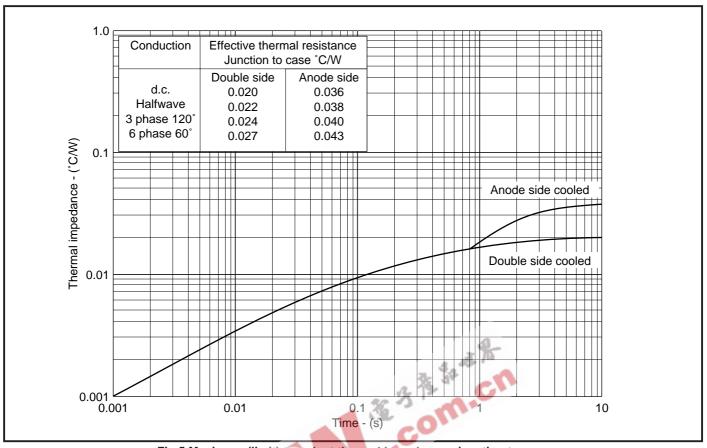


Fig.5 Maximum (limit) transient thermal impedance - junction to case

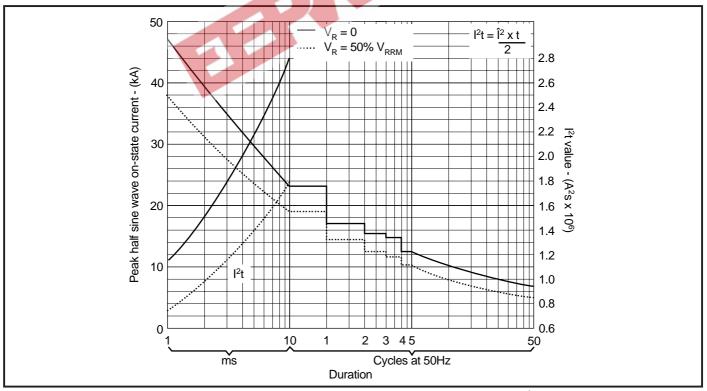
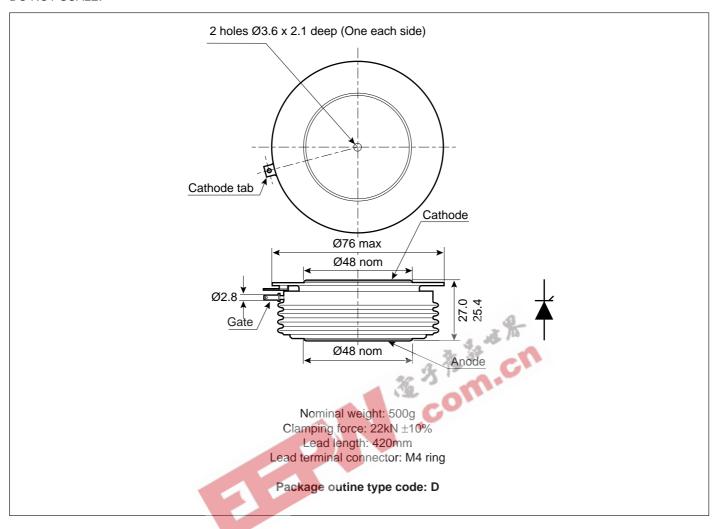


Fig.6 Surge (non-repetitive) on-state current vs time at T_{case} 125°C

PACKAGE DETAILS

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



ASSOCIATED PUBLICATIONS

Title	Application Note	
	Number	
Calculating the junction temperature or power semiconductors	AN4506	
Gate triggering and the use of gate characteristics	AN4840	
Recommendations for clamping power semiconductors	AN4839	
The effect of temperature on thyristor performance	AN4870	
Thyristor and diode measurement with a multi-meter	AN4853	
Turn-on performance of thyristors in parallel	AN4999	
Use of V_{TO} , r_{T} on-state characteristic	AN5001	

POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink / clamping systems in line with advances in device types and the voltage and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the up to date CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete solution (PACs).

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their safe operation. The PACs range offers a varied selection of preloaded clamps to suit all of our manufactured devices. This include cube clamps for single side cooling of 'T' 22mm

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

HEATSINKS

Power Assembly has it's own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance or our semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

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Target Information: This is the most tentative form of information and represents a very preliminary specification. No actual design work on the product has been started.

Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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